Amplifier Transistors NPN Silicon

COLLECTOR 3 BASE 1 EMITTER

MAXIMUM RATINGS

| Rating | Symbol | 2N5550 | 2N5551 | Unit |
|-----------------------------------------------------------------------|----------------------|-------------------|--------|----------------|
| Collector-Emitter Voltage | VCEO | 140 | 160 | Vdc |
| Collector-Base Voltage | V _{CBO} | 160 | 180 | Vdc |
| Emitter-Base Voltage | VEBO | 6.0 V | | |
| Collector Current — Continuous | IC | 600 | | mAdc |
| Total Device Dissipation @ T _A = 25°C Derate above 25°C | PD | 600 625 5.0 | | mW mW/°C |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | PD | 1.5 12 | | Watts mW/°C |
| Operating and Storage Junction Temperature Range | TJ, T _{stg} | -55 to +150 | | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|-----------------------------------------|-----------------|------|------|
| Thermal Resistance, Junction to Ambient | $R_{	heta JA}$ | 200 | °C/W |
| Thermal Resistance, Junction to Case | R_{θ} JC | 83.3 | °C/W |

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteris | stic | Symbol | Min | Max | Unit |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------|-----------------------|------------------|------------------------|--------------|
| OFF CHARACTERISTICS | | • | | | |
| Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 1.0 mAdc, I _B = 0) | 2N5550 2N5551 | V(BR)CEO | 140 160 | _ | Vdc |
| Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0) | 2N5550 2N5551 | V _(BR) CBO | 160 180 | | Vdc |
| Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0) | | V(BR)EBO | 6.0 | _ | Vdc |
| Collector Cutoff Current (V _{CB} = 100 Vdc, I _E = 0) (V _{CB} = 120 Vdc, I _E = 0) (V _{CB} = 100 Vdc, I _E = 0, T _A = 100°C) (V _{CB} = 120 Vdc, I _E = 0, T _A = 100°C) | 2N5550 2N5551 2N5550 2N5551 | ^I CBO | _ _ _ _ | 100 50 100 50 | nAdc μAdc |
| Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0) | | I _{EBO} | _ | 50 | nAdc |

^{1.} Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle = 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

2N5550 2N5551*

*Motorola Preferred Device





2N5550 2N5551

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

| Characteristic | | Symbol | Min | Max | Unit |
|-------------------------------------------------------------------------------------------------------------------------|------------------|----------------------|----------|--------------|------|
| ON CHARACTERISTICS(1) | | | | | |
| DC Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc) | 2N5550 2N5551 | hFE | 60 80 | _ | _ |
| $(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ | 2N5550 2N5551 | | 60 80 | 250 250 | |
| $(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ | 2N5550 2N5551 | | 20 30 | _ _ | |
| Collector-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) | Both Types | V _{CE(sat)} | _ | 0.15 | Vdc |
| $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$ | 2N5550 2N5551 | | _ | 0.25 0.20 | |
| Base-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) | Both Types | VBE(sat) | _ | 1.0 | Vdc |
| $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$ | 2N5550 2N5551 | | _ | 1.2 1.0 | |
| SMALL-SIGNAL CHARACTERISTICS | | | | | |
| Current-Gain — Bandwidth Product (IC = 10 mAdc, VCE = 10 Vdc, f = 100 MHz) | | fΤ | 100 | 300 | MHz |
| Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz) | | C _{obo} | _ | 6.0 | pF |
| Input Capacitance (VEB = 0.5 Vdc, I _C = 0 , f = 1.0 MHz) | 2N5550 2N5551 | C _{ibo} | | 30 20 | pF |
| Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) | | h _{fe} | 50 | 200 | _ |
| Noise Figure (I _C = 250 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz) | 2N5550 2N5551 | NF | | 10 8.0 | dB |

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

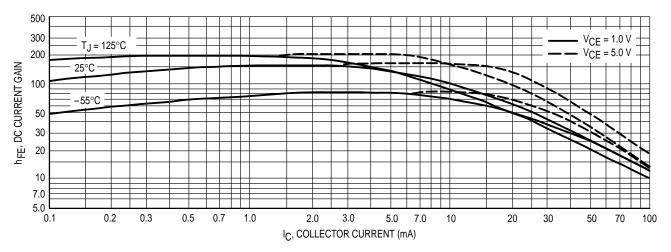


Figure 1. DC Current Gain

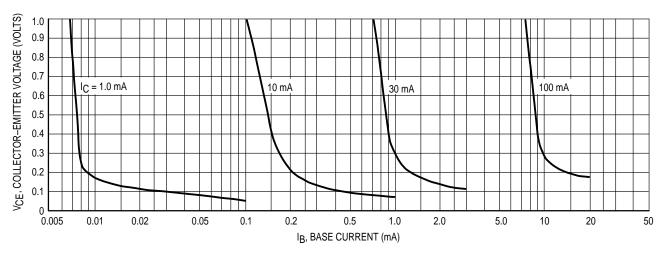


Figure 2. Collector Saturation Region

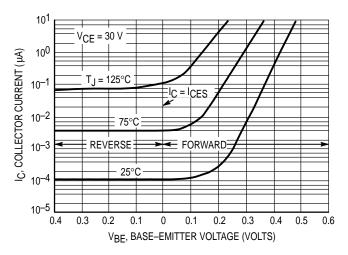


Figure 3. Collector Cut-Off Region

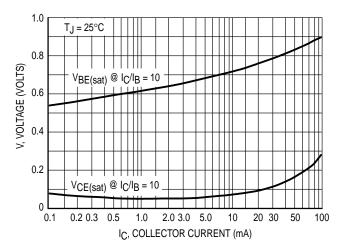


Figure 4. "On" Voltages

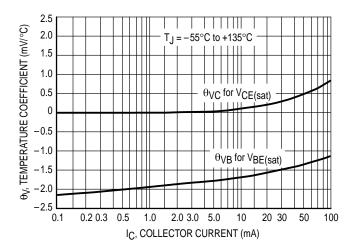


Figure 5. Temperature Coefficients

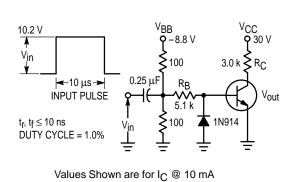


Figure 6. Switching Time Test Circuit

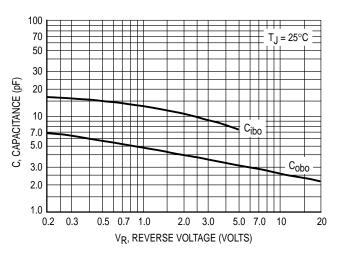


Figure 7. Capacitances

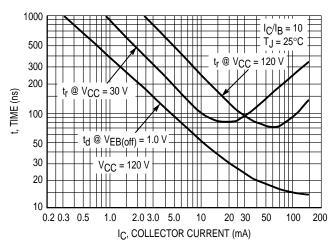


Figure 8. Turn-On Time

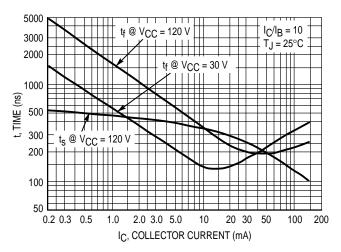
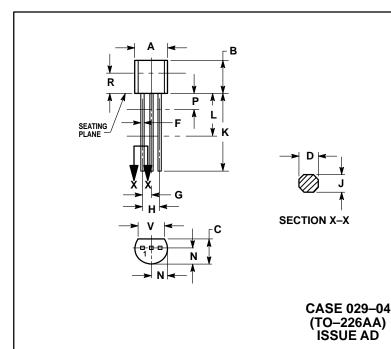


Figure 9. Turn-Off Time

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | INC | INCHES MIL | | IETERS |
|-----|-------|------------|-------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.175 | 0.205 | 4.45 | 5.20 |
| В | 0.170 | 0.210 | 4.32 | 5.33 |
| С | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.022 | 0.41 | 0.55 |
| F | 0.016 | 0.019 | 0.41 | 0.48 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| Н | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | | 12.70 | |
| L | 0.250 | | 6.35 | |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| Р | | 0.100 | | 2.54 |
| R | 0.115 | | 2.93 | |
| ٧ | 0.135 | | 3.43 | |

STYLE 1: PIN 1. EMITTER

2. BASE 3. COLLECTOR

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